AOT3N60

2.5A, 600V N-Channel MOSFET

formerly engineering part number AOT9602

RoHS Compliant

General Description

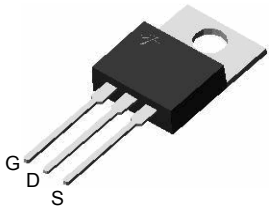
The AOT3N60 has been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.
By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

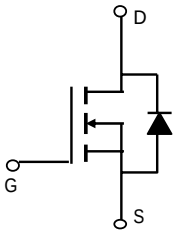
Features

V_{DS} (V) = 700V @ 150°C
I_D = 2.5A
$R_{DS(ON)}$ < 3.5 Ω (V_{GS} = 10V)

100% UIS Tested!
100% R_g Tested!
C_{iss}, C_{oss}, C_{rss} Tested!

Top View TO-220





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current [B]	T_C=25°C	I_D	2.5	A
	T_C=100°C		1.6	
Pulsed Drain Current [C]		I_{DM}	8	
Avalanche Current [C]		I_{AR}	2	A
Repetitive avalanche energy [C]		E_{AR}	60	mJ
Single pulsed avalanche energy [G]		E_{AS}	120	mJ
Peak diode recovery dv/dt		dv/dt	5	V/ns
Power Dissipation [B]	T_C=25°C	P_D	59.5	W
	Derate above 25°C		0.48	W/ °C
Junction and Storage Temperature Range		T_J, T_{STG}	-50 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient [A]	$R_{\theta JA}$	54	65	°C/W
Maximum Case-to-Sink [A]	$R_{\theta CS}$	-	0.5	°C/W
Maximum Junction-to-Case [D,F]	$R_{\theta JC}$	1.2	2.1	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	600			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		700		V
BV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D=250µA, V_{GS}=0V		0.65		V/ °C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V			1	µA
		V_{DS}=480V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	3	4	5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=1.25A		2.9	3.5	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=1.25A		2.8		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.64	1	V
I_S	Maximum Body-Diode Continuous Current				2	A
I_{SM}	Maximum Body-Diode Pulsed Current				8	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz	240	304	370	pF
C_{oss}	Output Capacitance		25	31.4	38	pF
C_{rss}	Reverse Transfer Capacitance		2.6	3.3	4	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	2.3	2.9	4.5	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=2A		9.9	12	nC
Q_{gs}	Gate Source Charge			2.1	3	nC
Q_{gd}	Gate Drain Charge			4.6	6	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=300V, I_D=2A, R_G=25Ω		17	20	ns
t_r	Turn-On Rise Time			17	20	ns
$t_{D(off)}$	Turn-Off DelayTime			24	30	ns
t_f	Turn-Off Fall Time			16	20	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=2.5A,dI/dt=100A/µs,V_{DS}=100V		175	210	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=2.5A,dI/dt=100A/µs,V_{DS}=100V		1.4	1.7	µC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A=25°C.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C.

G. L=60mH, I_{AS}=2A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

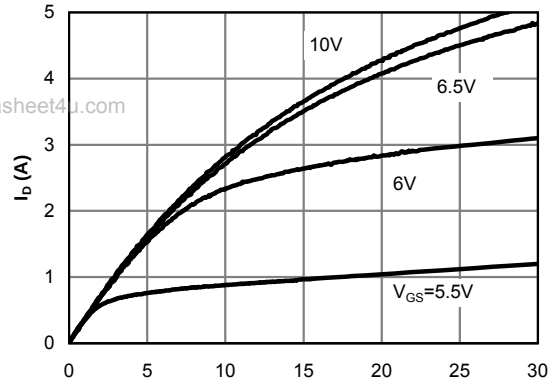


Fig 1: On-Region Characteristics

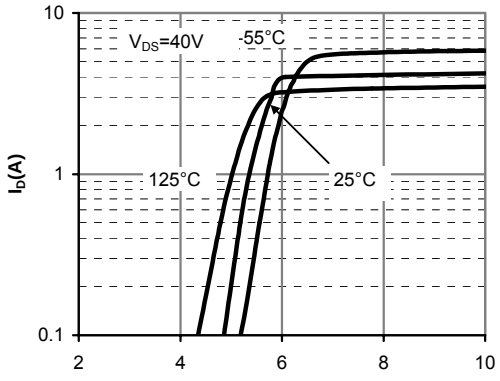


Figure 2: Transfer Characteristics

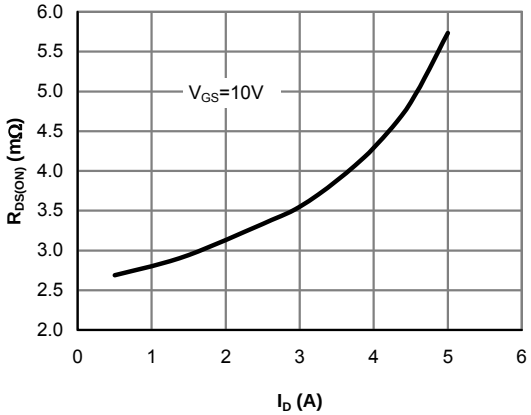


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

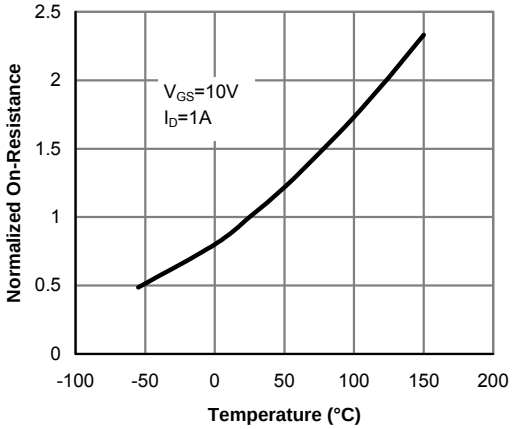


Figure 4: On-Resistance vs. Junction Temperature

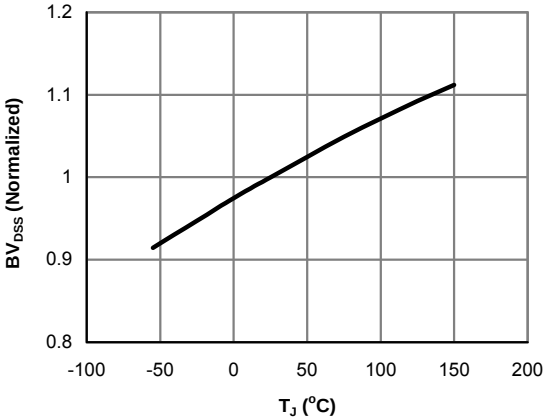


Figure 5: Break Down vs. Junction Temperature

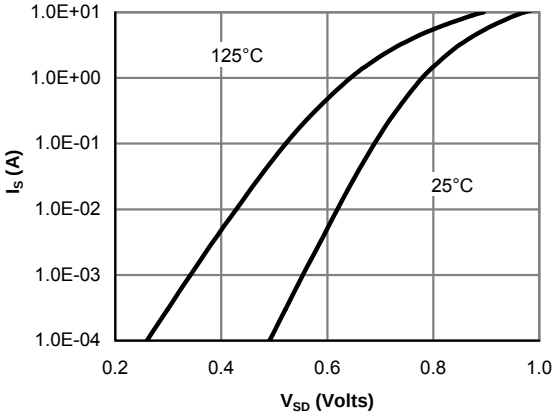


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

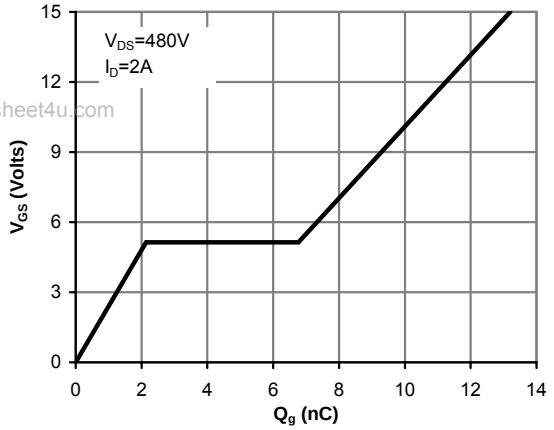


Figure 7: Gate-Charge Characteristics

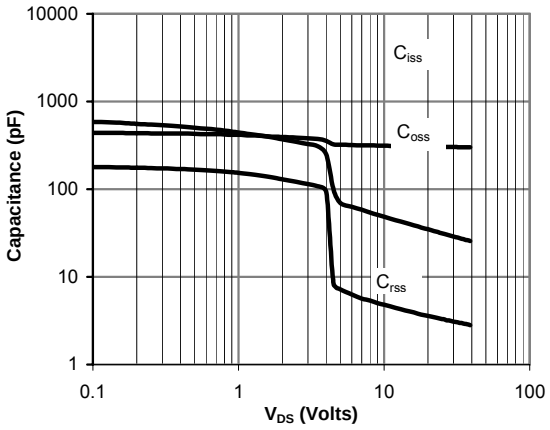


Figure 8: Capacitance Characteristics

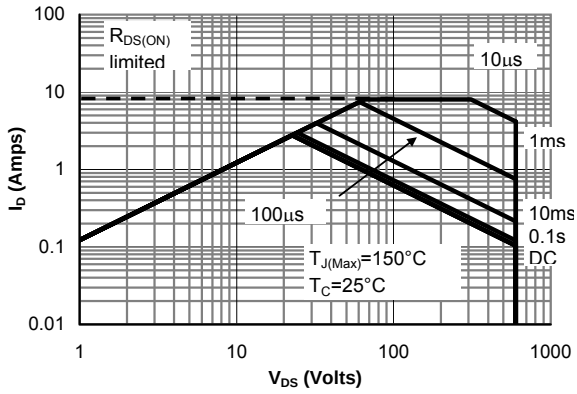


Figure 9: Maximum Forward Biased Safe Operating Area for AOT3N60 (Note F)

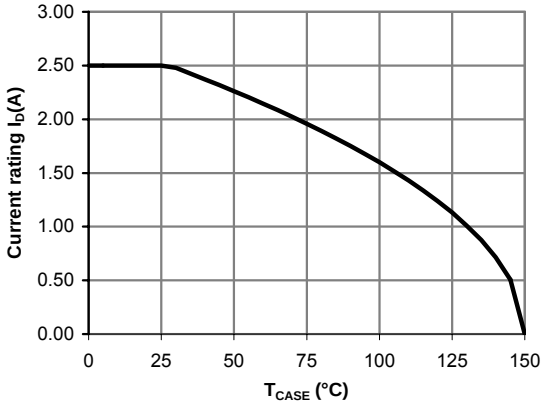


Figure 10: Current De-rating (Note B)

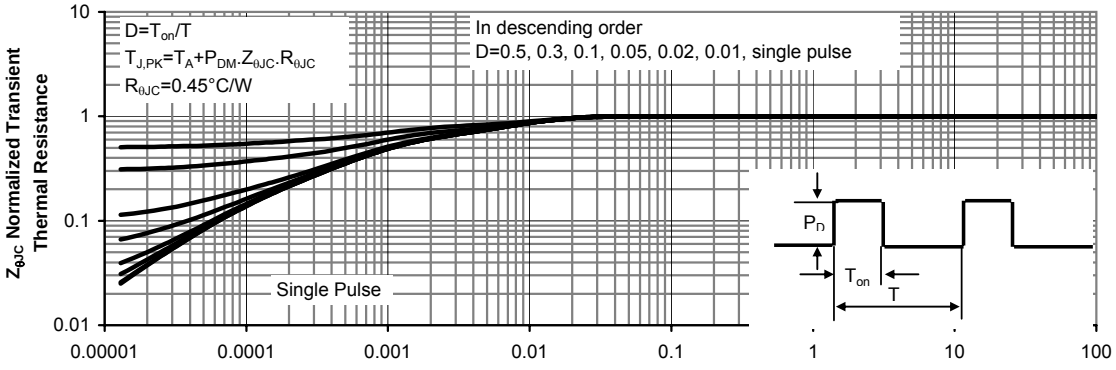
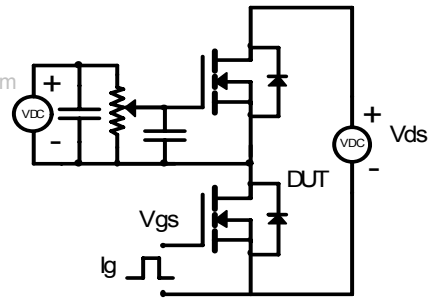
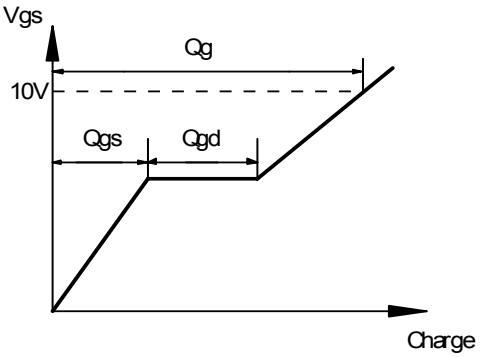


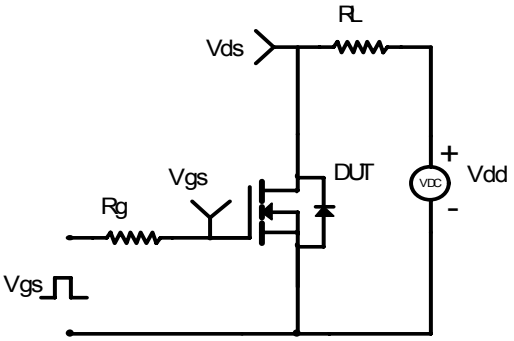
Figure 11: Normalized Maximum Transient Thermal Impedance for AOT3N60 (Note F)

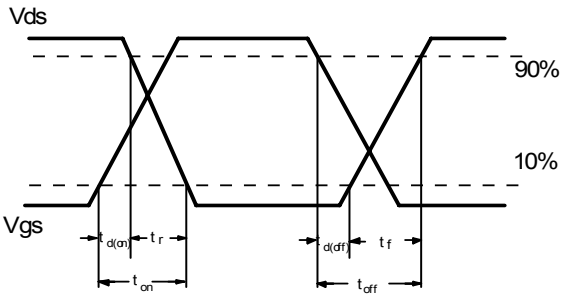
Gate Charge Test Circuit & Waveform



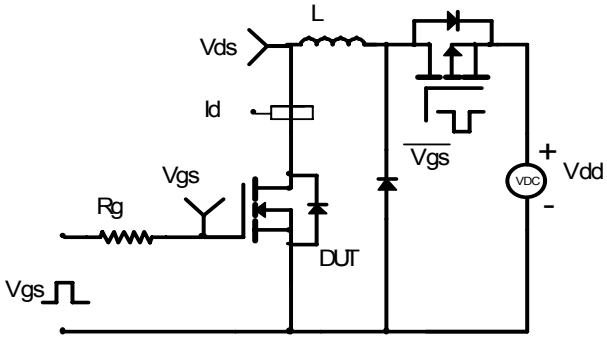


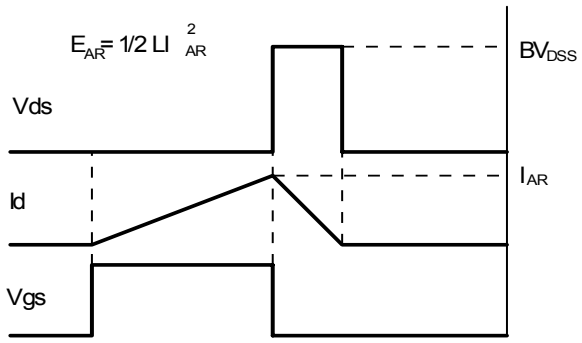
Resistive Switching Test Circuit & Waveforms





Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms